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Lead-free Green

DMN3731U

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	Max $R_{DS(ON)}$	I_D Max T_A = +25°C
30V	460mΩ @ V_{GS}= 4.5V	0.9A
	560mΩ @ V_{GS}= 2.5V	0.83A

Features and Benefits

- Low $V_{GS(TH)}$, can be Driven Directly from a Battery
- Low $R_{DS(ON)}$
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

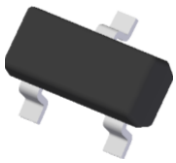
- Load Switch
- Portable Applications
- Power Management Functions

Mechanical Data

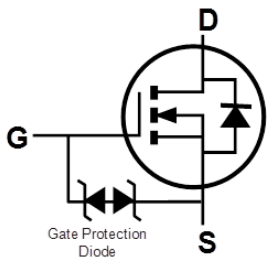
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



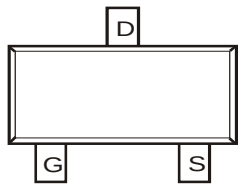
SOT23



Top View



Equivalent Circuit



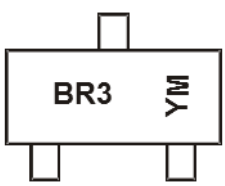
Top View
Pin-Out

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Quantity per Reel
DMN3731U-7	BR3	7	3,000
DMN3731U-13	BR3	13	10,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BR3 = Product Type Marking Code
YM or $\overline{Y}\overline{M}$ = Date Code Marking
Y or $\overline{Y}$ =Year (ex: G = 2019)
M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024
Code	F	G	H	I	J	K	L

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = 25°C unless otherwise specified)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	0.9 0.7	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.55	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	3	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	303	°C/W
Total Power Dissipation (Note 6)		P_D	0.58	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	215	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 10µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	3	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.45	—	0.95	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	271	460	mΩ	V_{GS} = 4.5V, I_D = 200mA
			288	560		V_{GS} = 2.5V, I_D = 100mA
			324	730		V_{GS} = 1.8V, I_D = 75mA
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	73	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	7.2	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	5	—	pF	
Gate Resistance	R_g	—	902	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	5.5	—	nC	V_{GS} = 4.5V, V_{DS} = 15V, I_D = 1A
Gate-Source Charge	Q_{gs}	—	0.8	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.4	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	2.5	—	ns	V_{DS} = 10V, I_D = 1A, V_{GS} = 10V, R_g = 6Ω
Turn-On Rise Time	t_R	—	3.1	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	477	—	ns	
Turn-Off Fall Time	t_F	—	123	—	ns	
Reverse Recovery Time	t_{RR}	—	59	—	ns	I_F = 1A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	25	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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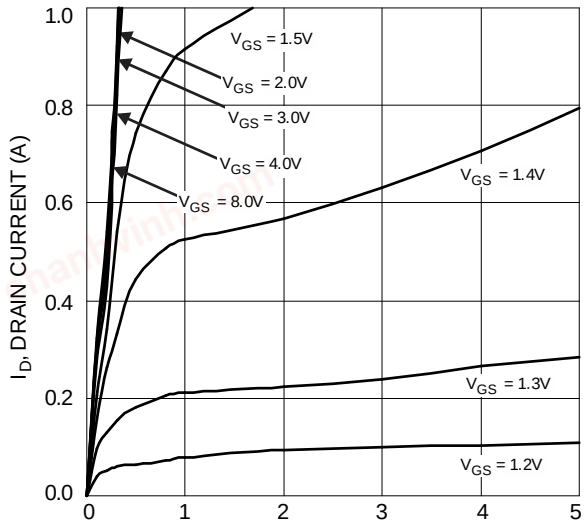


Figure 1 Typical Output Characteristic

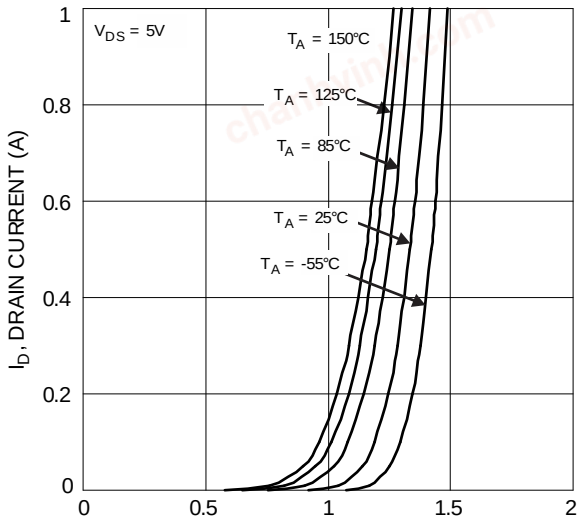


Figure 2 Typical Transfer Characteristics

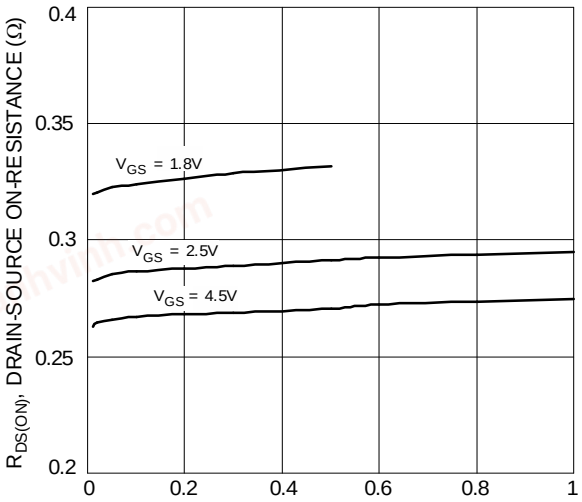


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

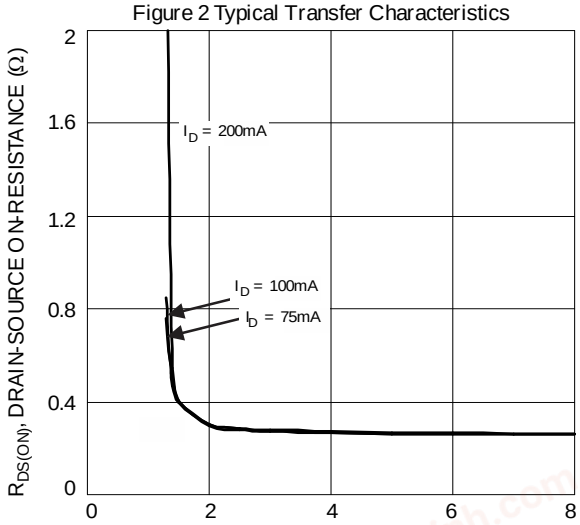


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

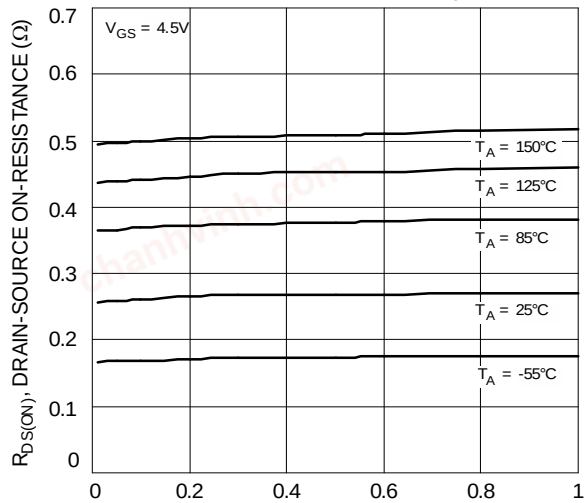


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

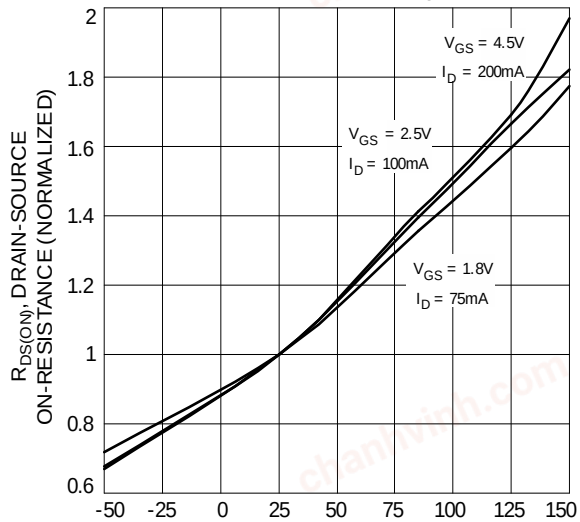


Figure 6 On-Resistance Variation with Temperature

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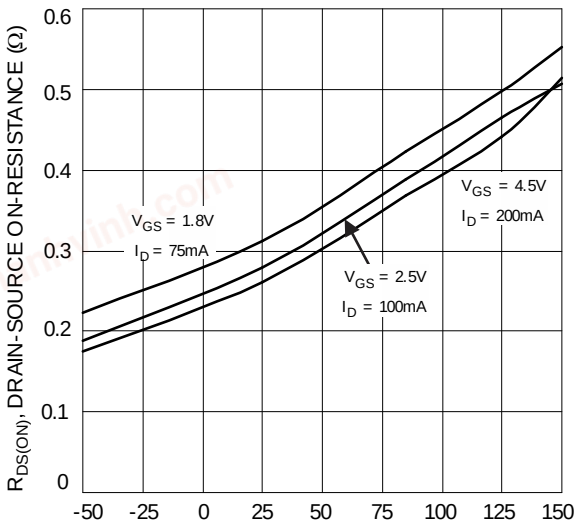


Figure 7 On-Resistance Variation with Temperature

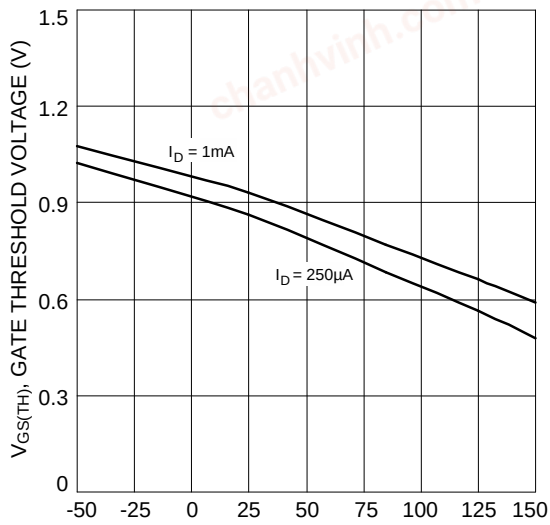


Figure 8 Gate Threshold Variation vs. Junction Temperature

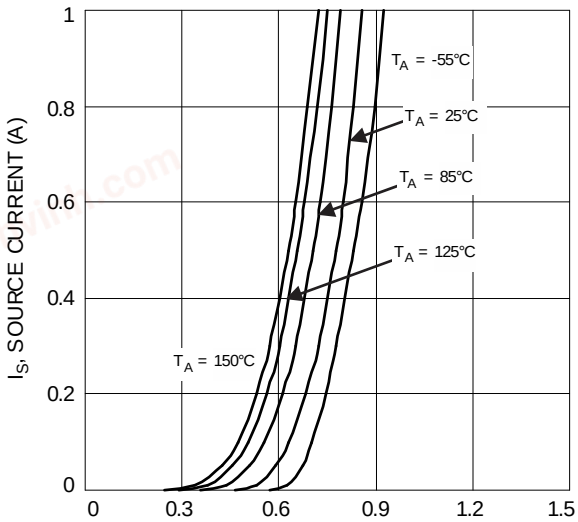


Figure 9 Diode Forward Voltage vs. Current

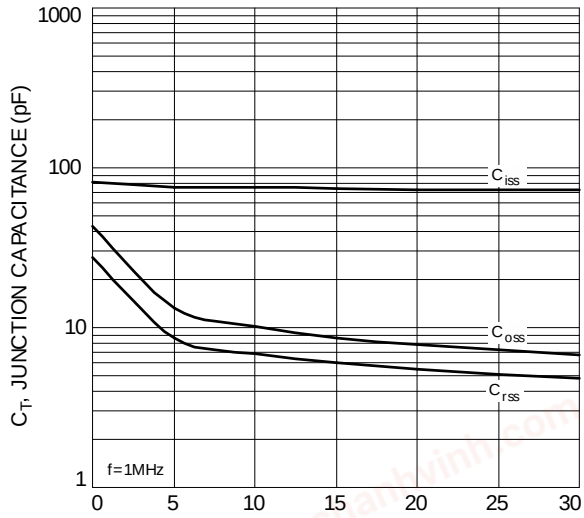


Figure 10 Typical Junction Capacitance

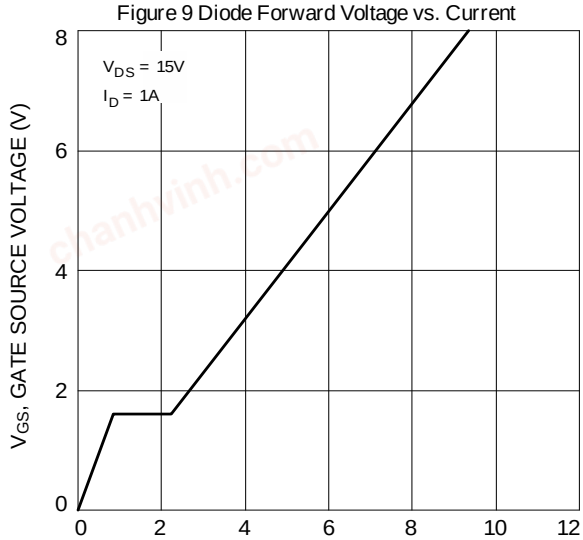


Figure 11 Gate Charge

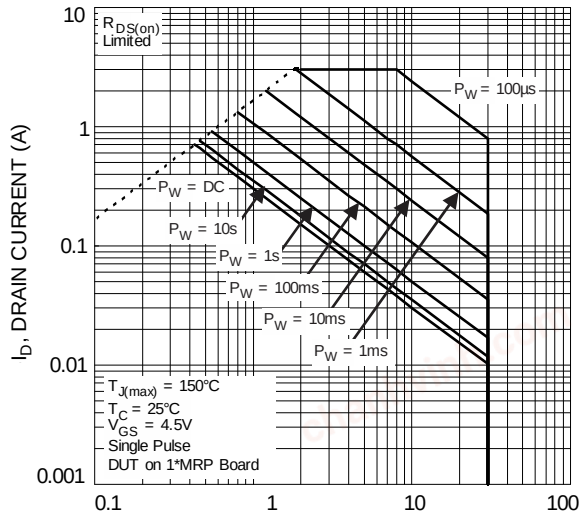


Figure # SOA, Safe Operation Area

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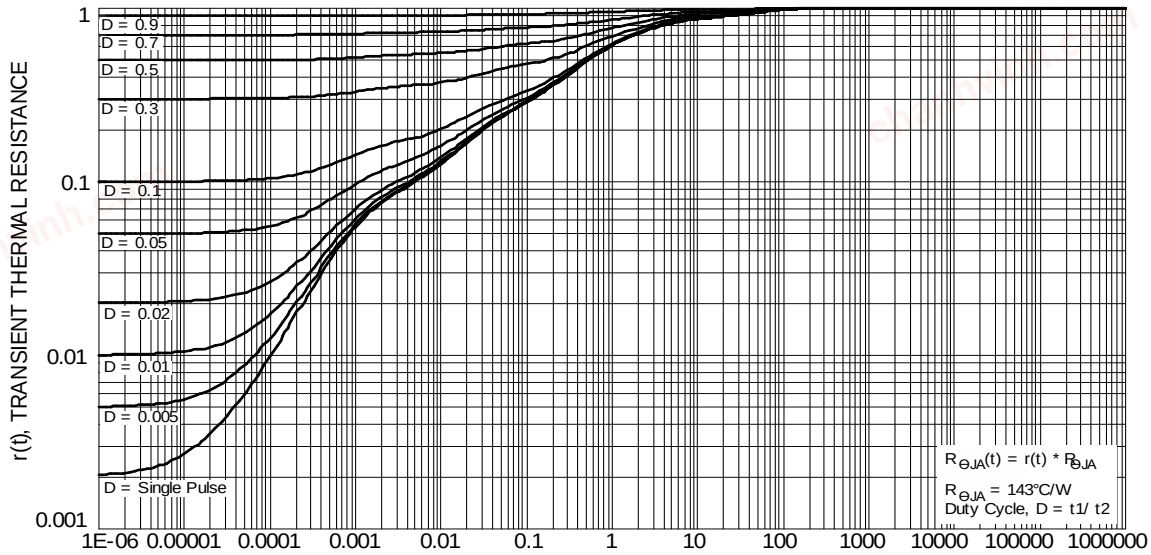


Figure 13 Transient Thermal Resistance

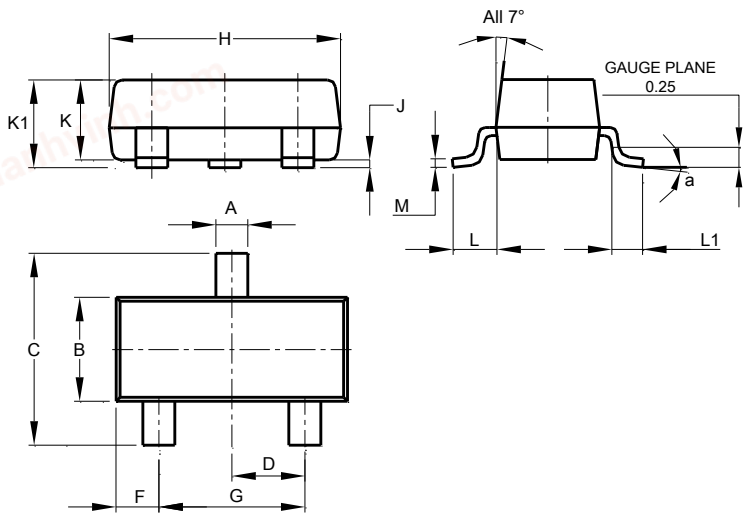
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

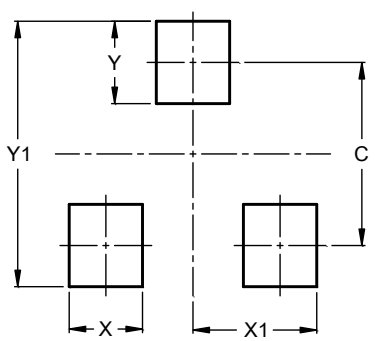


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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